

SANYO

No.4748

2SJ273

P-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

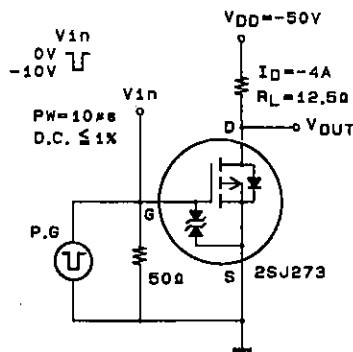
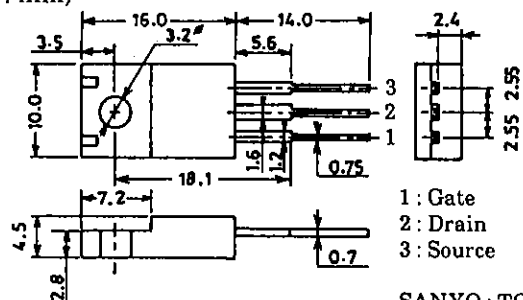
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Drain-to-Source Voltage	V_{DSS}		-100	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current(DC)	I_D		-6	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-24	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c = 25^\circ C$	25	W
Channel Temperature	T_{ch}		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

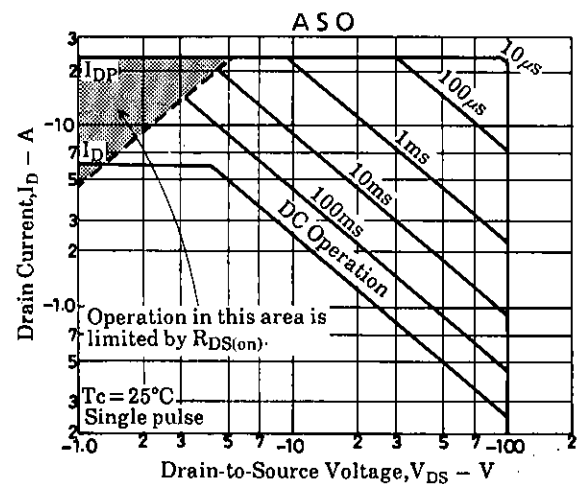
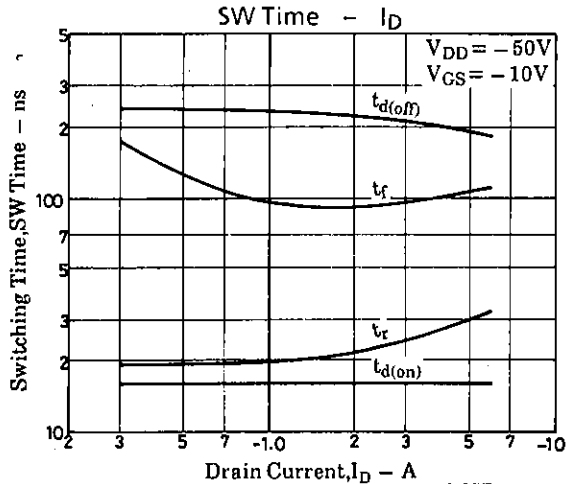
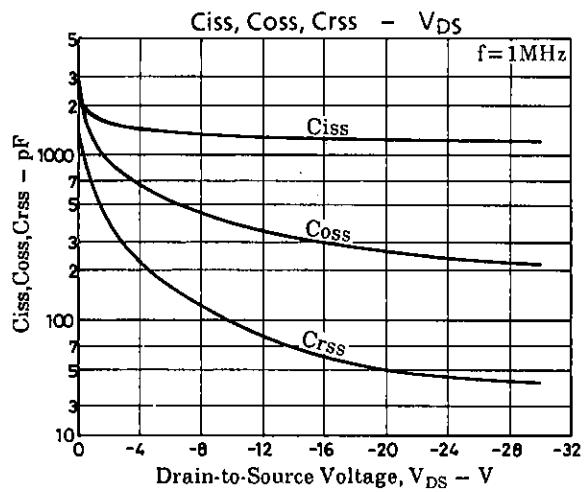
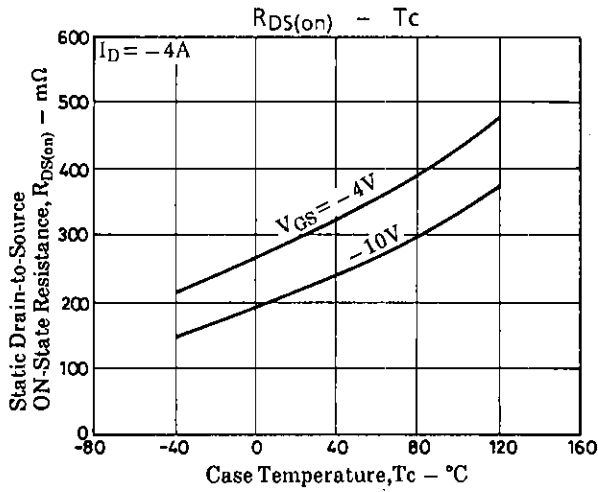
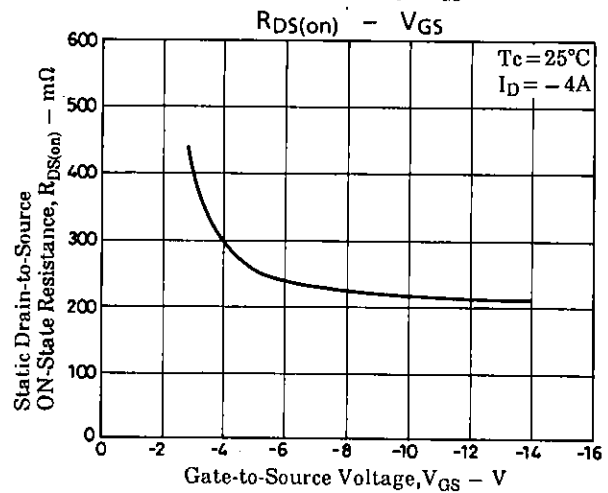
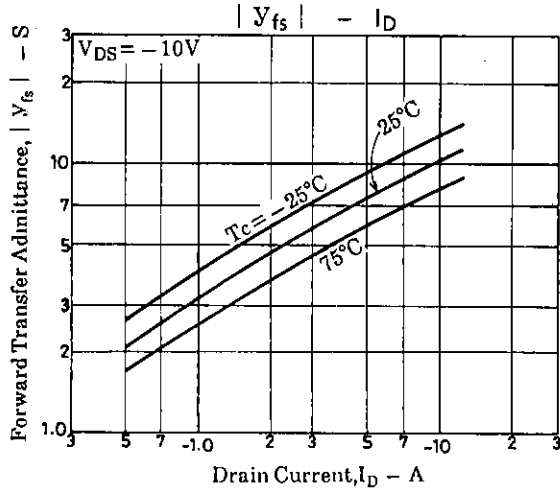
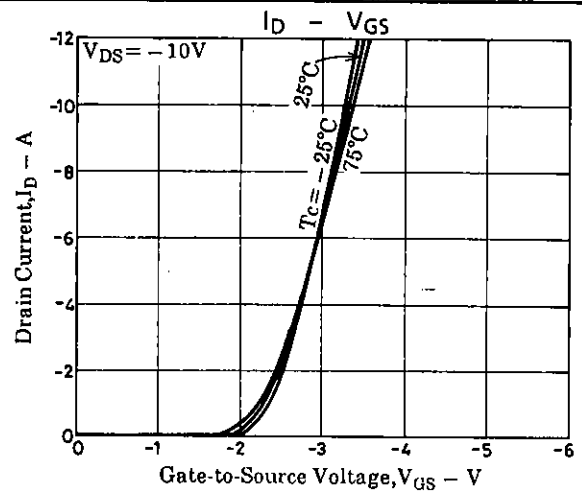
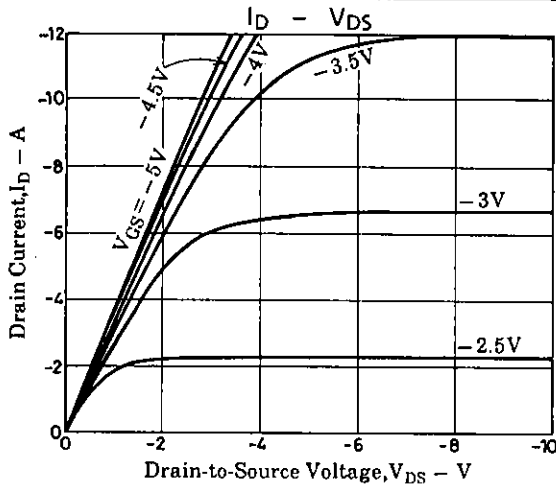
Electrical Characteristics at $T_a = 25^\circ\text{C}$

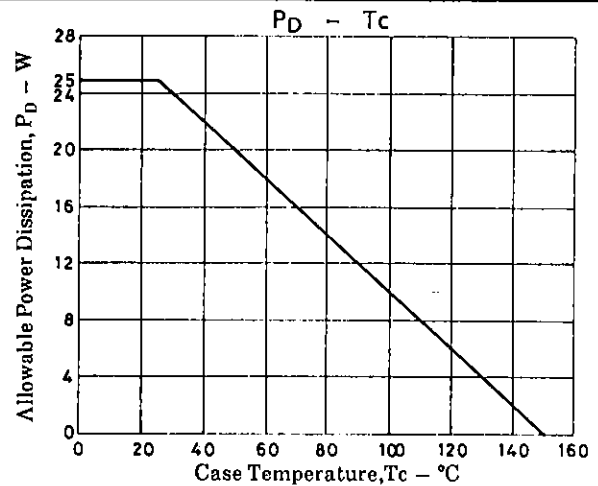
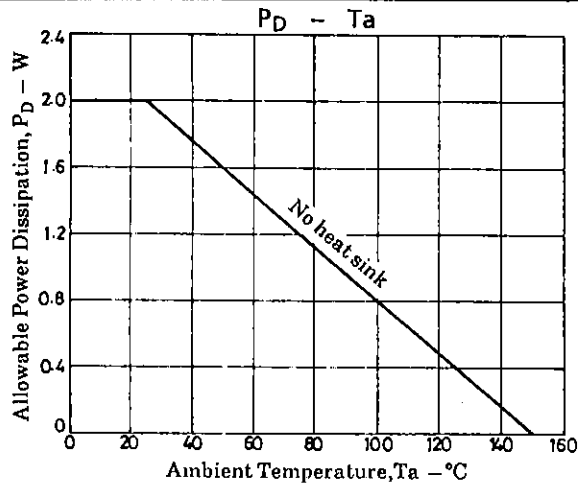
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-100			V
G-S Breakdown Voltage	$V_{(BR)GS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{V}, V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -4\text{A}$	3.5	6.5		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -10\text{V}$	0.22	0.3		Ω
	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -4\text{V}$	0.3	0.4		Ω
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$	1230			pF
Output Capacitance	C_{oss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$	260			pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$	50			pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.	16			ns
Rise Time	t_r	"	27			ns
Turn-OFF Delay Time	$t_{d(off)}$	"	200			ns
Fall Time	t_f	"	100			ns
Diode Forward Voltage	V_{SD}	$I_S = -6\text{A}, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit**Package Dimensions 2063A**
(unit : mm)

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